

TRANSISTOR (PNP)

**FEATURES**

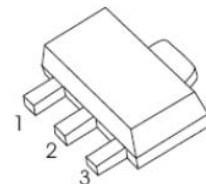
- High voltage
- High transition frequency
- **Pb-Free package is available**  
 RoHS product for packing code suffix "G"  
 Halogen free product for packing code suffix "H"

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-120	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-120	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current -Continuous	-0.8	A
P <sub>C</sub>	Collector Power Dissipation	0.5	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

**SOT-89**

1. BASE
2. COLLECTOR
3. EMITTER


**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-1mA, I <sub>E</sub> =0	-120			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> =0	-120			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-1mA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-120V, I <sub>E</sub> =0			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0			-0.1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-100mA	80		240	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA			-1	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-500mA			-1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-100mA		120		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz			30	pF

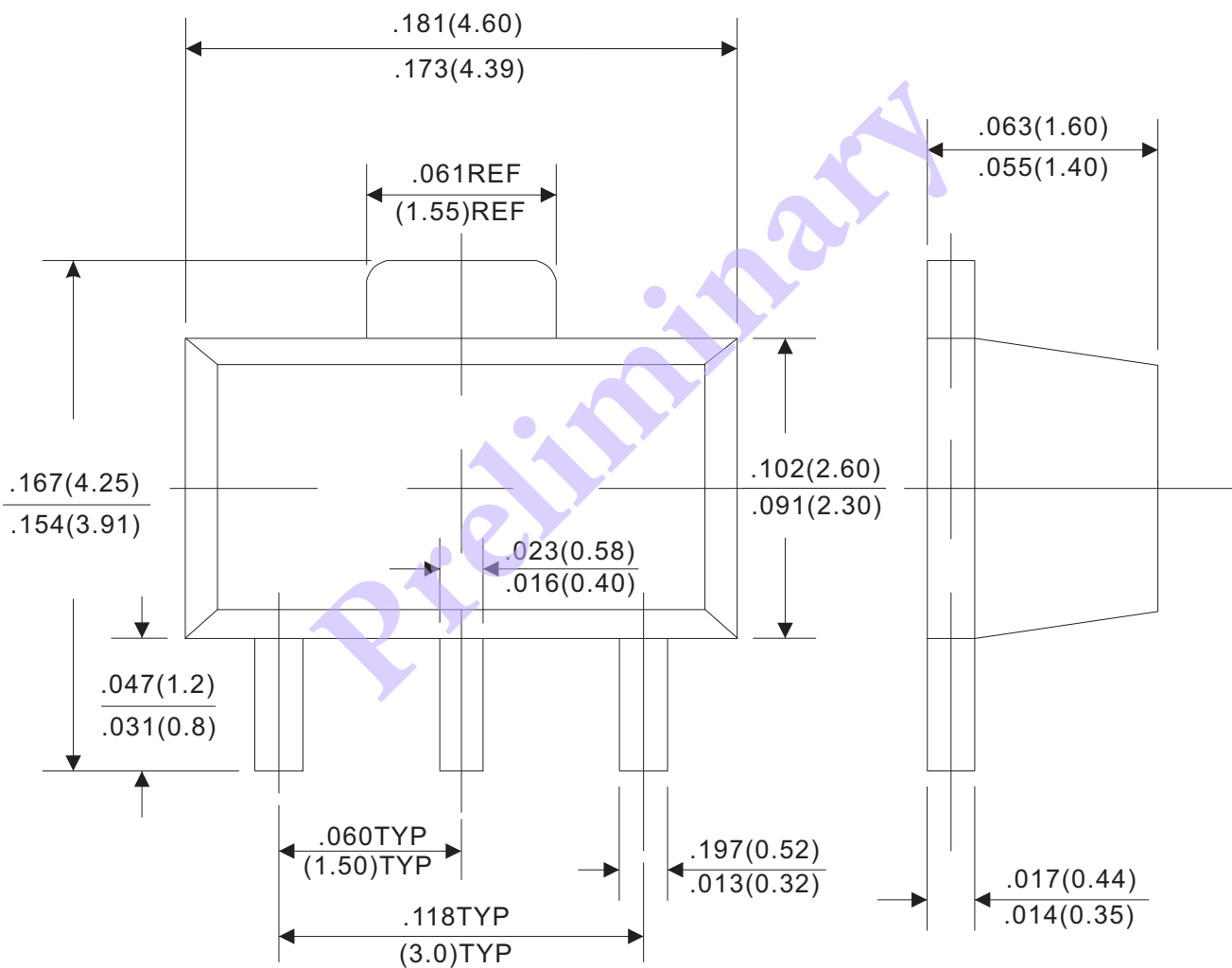
**CLASSIFICATION OF h<sub>FE</sub>**

Rank	O	Y
Range	80-160	120-240
Marking	DO	DY



# Outline Drawing

# SOT-89



Dimensions in inches and (millimeters)

Rev.C